

Bi-Directional P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY					
V _{S1S2} (V)	$R_{S1S2(on)}(\Omega)$	I _{S1S2} (A)			
	0.060 at V _{GS} = - 4.5 V	- 4.4			
- 20	0.080 at V _{GS} = - 2.5 V	- 3.9			
	0.105 at V _{GS} = - 1.8 V	- 3.4			

FEATURES

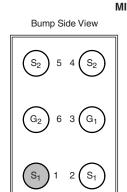
- TrenchFET® Power MOSFET
- Ultra-Low R_{SS(on)}
- ESD Protected: 6000 V
- MICRO FOOT[®] Chipscale Packaging Reduces Footprint Area, Profile (0.65 mm) and On-Resistance Per Footprint Area

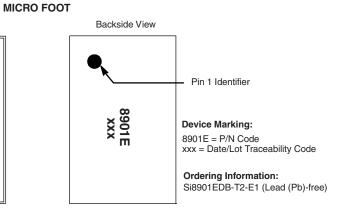


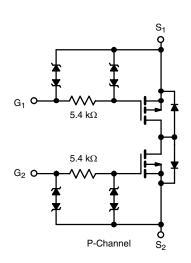
ROHS

APPLICATIONS

· Smart Batteries for Portable Devices







ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted						
Parameter	Symbol	5 s	Steady State	Unit		
Source1- Source2 Voltage		V _{S1S2}	- 20		V	
Gate-Source Voltage		V _{GS}	± 12			
Continuous Convent Convent (T. 150 °C)	T _A = 25 °C	1	- 4.4	- 3.5	А	
Continuous Source1- Source2 Current (T _J = 150 °C) ^a	T _A = 85 °C	- I _{S1S2}	- 3.2	- 2.5		
Pulsed Source1- Source2 Current		I _{SM}	- 10			
M	T _A = 25 °C	В	1.7 1		W	
Maximum Power Dissipation ^a	T _A = 85 °C	- P _D	0.8	0.5	VV	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55	to 150	°C	
Package Reflow Conditions ^c IR/Convection				260		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
	t ≤ 5 s	B	60	75		
Maximum Junction-to-Ambient ^a	Steady State	R_{thJA}	95	120	°C/W	
Maximum Junction-to-Foot ^b	Steady State	R _{thJF}	18	22		

Notes:

- a. Surface Mounted on 1" x 1" FR4 board.
- b. The foot is defined as the top surface of the package.
- c. Refer to IPC/JEDEC (J-STD-020C), no manual or hand soldering.

Vishay Siliconix



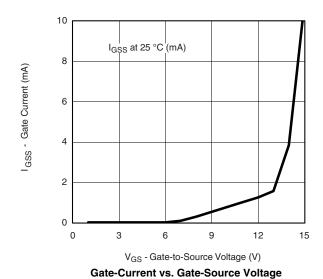
SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions		Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{SS} = V_{GS}$, $I_D = -350 \mu A$	- 0.45		- 1.0	٧	
Gate-Body Leakage		$V_{SS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$			± 4	μΑ	
Gale-Body Leakage	I _{GSS}	$V_{SS} = 0 V, V_{GS} = \pm 12 V$			± 10	mA	
Zana Oata Vallana Oamaa Oamaat	la	V _{SS} = - 20 V, V _{GS} = 0 V			- 1	μΑ	
Zero Gate Voltage Source Current	I _{S1S2}	$V_{SS} = -20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 85 ^{\circ}\text{C}$			- 5		
On-State Source Current ^a	I _{S(on)}	V _{SS} = - 5 V, V _{GS} = - 4.5 V	- 5			Α	
		V _{GS} = - 4.5 V, I _{SS} = - 1 A		0.048	0.060		
Source1- Source2 On-State Resistance ^a	R _{S1S2(on)}	V _{GS} = - 2.5 V, I _{SS} = - 1 A		0.062	0.080	Ω	
		V _{GS} = - 1.8 V, I _{SS} = - 1 A		0.081	0.105		
Forward Transconductance ^a	9 _{fs}	V _{SS} = - 10 V, I _{SS} = - 1 A		7		S	
Dynamic ^b							
Turn-On Delay Time	t _{d(on)}			2.3	3.5		
Rise Time	t _r	V_{SS} = - 10 V, R_L = 10 Ω		2.2	3.5	110	
Turn-Off Delay Time	t _{d(off)}	$t_{d(off)}$ $I_{SS} \cong -1 \text{ A, } V_{GEN} = -4.5 \text{ V, } R_g = 6 \Omega$		1.3	2	μs	
Fall Time	t _f			9	14		

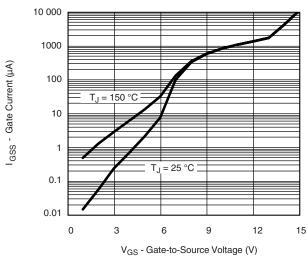
Notes:

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





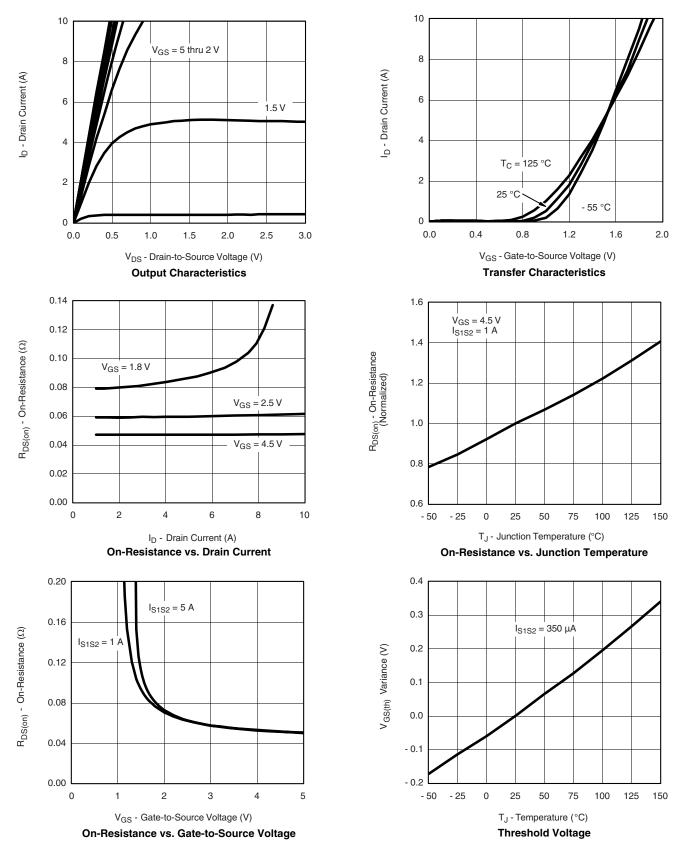
Gate Current vs. Gate-Source Voltage





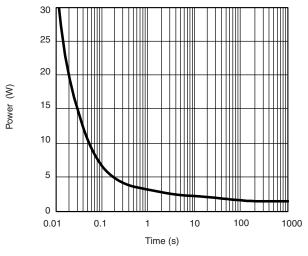


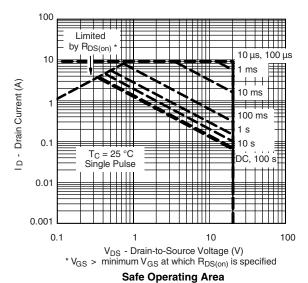
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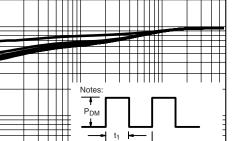
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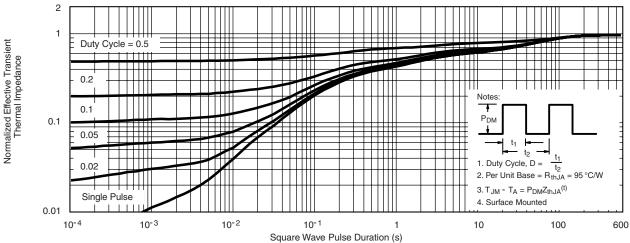
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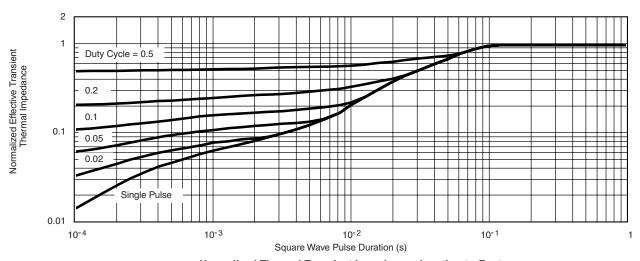


Single Pulse Power, Junction-to-Ambient





Normalized Thermal Transient Impedance, Junction-to-Ambient

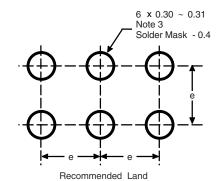


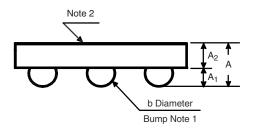
Normalized Thermal Transient Impedance, Junction-to-Foot

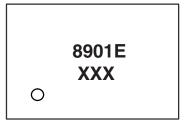


PACKAGE OUTLINE

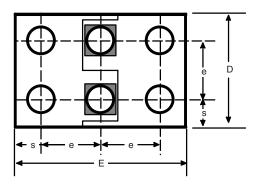
MICRO FOOT: 6-BUMP (2 x 3, 0.8 mm PITCH)







Mark on Backside of Die



Notes (Unless Otherwise Specified):

- 1. 6 solder bumps are 95.5/3.8/0.7 Sn/Ag/Cu.
- 2. Backside surface is coated with a Ag/Ni/Ti layer.
- 3. Non-solder mask defined copper landing pad.
- 4. Laser marks on the silicon die back.

Dim.	Millimeters ^a		Inches		
	Min.	Max.	Min.	Max.	
Α	0.600	0.650	0.0236	0.0256	
A ₁	0.260	0.290	0.102	0.114	
A ₂	0.340	0.360	0.0134	0.0142	
b	0.370	0.410	0.0146	0.0161	
D	1.52	1.6	0.0598	0.0630	
E	2.32	2.4	0.0913	0.0945	
е	0.750	0.850	0.0295	0.0335	
s	0.380	0.400	0.0150	0.0157	

Notes:

a. Use millimeters as the primary measurement.

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